

A1 end
substrate is pre-processed by dipping it in a water-based hydrofluoric acid solution. The wafer is then placed in the deposition chamber and baked at about 900°C for approximately one minute.

Please replace paragraph 52 with the following:

A2
[0052] Where lower temperatures are desired, a dedicated pre-clean chamber such as the one used in the Epi Centura system available from Applied Materials of Santa Clara, CA, may be used to perform the cleaning step. In this case, the wafer is first dipped in a water-based solution of hydrofluoric acid. Next, the wafer is placed in the pre-clean chamber and baked at a first temperature for a predetermined time interval and then baked at a second temperature for a second predetermined time interval. In one instance, the first bake is performed at about 750°C - 770°C and the second bake is performed at temperatures in the range of about 770°C - 795°C.

Please replace paragraph 53 with the following:

A3
[0053] The cleaned substrate 210 is then loaded on susceptor 20 between domes 14 and 16 (Step 530). Next, chamber 12 is heated to the desired temperature using the high intensity lamps 34. (Step 540). Preferably, chamber 12 is heated to a temperature between about 550°C and 1200°C. More preferably, chamber 12 is heated to about 850°C - 1000°C. The first and second source gases 130 and 132 and dilutant gas 134 are next introduced into chamber 12. (Step 550). The pressure in chamber 12 is then adjusted until the desired pressure is reached. (Step 560). For low pressure CVD, the pressure in chamber 12 is maintained below 760 Torr. Although Steps 540, 550 and 560 have been described as having been performed in a particular sequence, those skilled in the art will recognize that these steps may be performed in any order.

IN THE CLAIMS

Amendments to the claims, with insertions underlined and deletions bracketed, is attached as Appendix B. A clean copy of the claims that will be pending upon entry of this amendment is attached as Appendix C.